



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Transistors

UMZ1N Multi-Chip TRANSISTOR (NPN/PNP)

FEATURES

Power dissipation

P_{CM} : 150 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 150/-150 mA

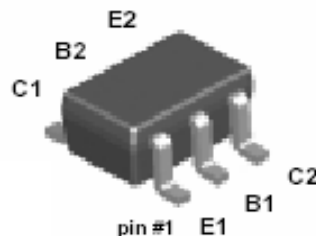
Collector-base voltage

$V_{(BR)CBO}$: 60/-60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-363



TR1(NPN) ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu A, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6V, I_C=1mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.4	V
Transition frequency	f_T	$V_{CE}=12V, I_C=2mA, f=100MHz$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=12V, I_E=0, f=1MHz$		2	3.5	pF

TR2(PNP) ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-6V, I_C=-1mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50mA, I_B=-5mA$			-0.5	V
Transition frequency	f_T	$V_{CE}=-12V, I_C=2mA, f=100MHz$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-12V, I_E=0, f=1MHz$		4	5	pF

